

Listing of Claims:

Claims 1-33 (canceled)

34. (currently amended) A bond pad structure, comprising:

a semiconductor substrate;

~~a plurality of conductive bond pads,~~ comprising interlocking grid structures, formed over said semiconductor substrate;

a passivating layer formed over said ~~bond pads,~~ interlocking grid structures, having multiple openings to each said interlocking grid structures ~~bond pads;~~

a barrier layer formed over said passivating layer and in said openings;

a conducting pad formed over each said ~~bond pad~~ interlocking grid structures and over said barrier layer, whereby an upper surface of said conductive pad provides improved adhesion for subsequently formed bonds.

35. (currently amended) The bond pad structure of Claim 34, wherein said conductive bond ~~pads are~~ pad is formed of copper.

36. (original) The bond pad structure of Claim 34, wherein said passivating layer is selected from the group consisting of silicon oxide, silicon nitride and polyimide.

37. (currently amended) The bond pad structure of Claim 34, wherein said bond pad forms an interlocking grid array in the bond pad via contact region, which is approximately 100 by 100 microns square and the size ~~off~~ of the island structures are from about 10 to 25 microns in width, approximately 4 microns in height, and from about 4 to 10 in number, ~~per said conducting bond pad,~~ of interlocking grid structures, increasing surface area for improved adhesion.

38. (currently amended) The bond pad structure of Claim 34, wherein said conductive bond ~~pads are~~ pad is formed of aluminum.

39. (original) The bond pad structure of Claim 34, wherein said barrier layer is formed of tantalum nitride.